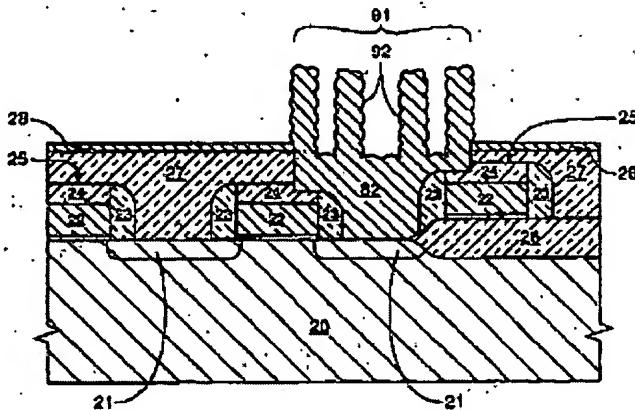


**Conducting structure prodn. on topography of substrate**

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- **international:** H01L21/8242  
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[Report a data error here](#)**Abstract of DE4447804**

Prodn. of a conducting structure having several pins on the topography of a starting substrate comprises: (a) forming 1st, 2nd and 3rd insulating layers (27,28,29) completely over the topography; (b) patterning and etching an opening (30) in the 3 insulating layers; (c) forming and planarising a conducting layer (31) by filling the opening; (d) creating an etching mask (33) by applying polysilicon having semispherical grain size for pattern transfer; (e) transferring an archipelago pattern over the etching mask onto the planar conducting layer; and (f) forming pins (34) to create the conducting structure having the several pins.



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